



深圳市龙晶微电子有限公司

SOT-23 Plastic-Encapsulate Transistors

S9012 TRANSISTOR (PNP)

FEATURES

- Complementary to S9013
- Excellent h_{FE} linearity

MARKING: 2T1

SOT-23



1. BASE
2. EMITTER
3. COLLECTOR

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-500	mA
P_C	Collector Power Dissipation	300	mW
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100 \mu\text{A}$, $I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}$, $I_B = 0$	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100 \mu\text{A}$, $I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -40\text{V}$, $I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -20\text{V}$, $I_B = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V}$, $I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -1\text{V}$, $I_C = -50\text{mA}$	120		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{mA}$, $I_B = -50\text{mA}$			-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500\text{mA}$, $I_B = -50\text{mA}$			-1.2	V
Transition frequency	f_T	$V_{CE} = -6\text{V}$, $I_C = -20\text{mA}$ $f = 30\text{MHz}$	150			MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$			5	pF

CLASSIFICATION OF h_{FE}

Rank	L		
Range	200-350		

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